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Kind regards,

Team Nexperia



# PDTB123ET

PNP 500 mA, 50 V resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

Rev. 3 — 22 September 2010

**Product data sheet** 

## 1. Product profile

### 1.1 General description

500 mA PNP Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTD123ET.

#### 1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- AEC-Q101 qualified

### 1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC807 series in digital applications
- Switching loads

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	



PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## 2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)	[3]	3
3	output (collector)	1 2 006aaa144	1 R1 R2 2
		000dda1777	sym003

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTB123ET	-	plastic surface-mounted package; 3 leads	SOT23

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PDTB123ET	*7S

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-12	V
Io	output current		-	-500	mA

### PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$P_{tot}$	total power dissipation	$T_{amb} \leq 25~^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

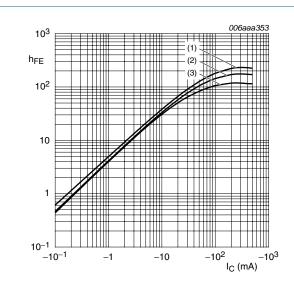
### 7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$	-	-	-0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-2.0	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -50 \text{ mA}$	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -50 \text{ mA};$ $I_B = -2.5 \text{ mA}$	-	-	-0.3	V
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -100  \mu\text{A}$	-0.6	-1.1	-1.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$	-1.0	-1.5	-2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 100  MHz	-	11	-	pF

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 



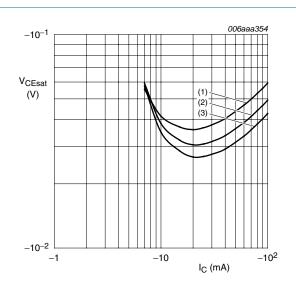
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



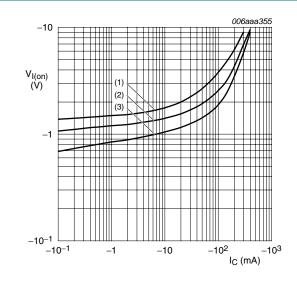
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



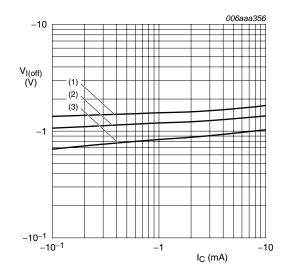
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

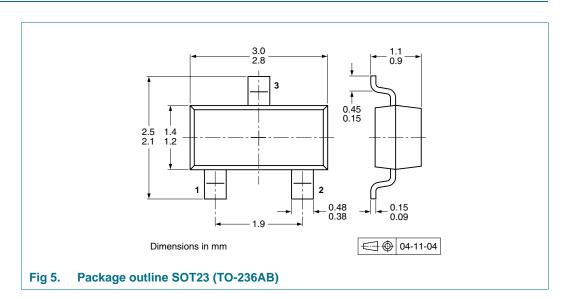
PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

Table 8. Packing methods

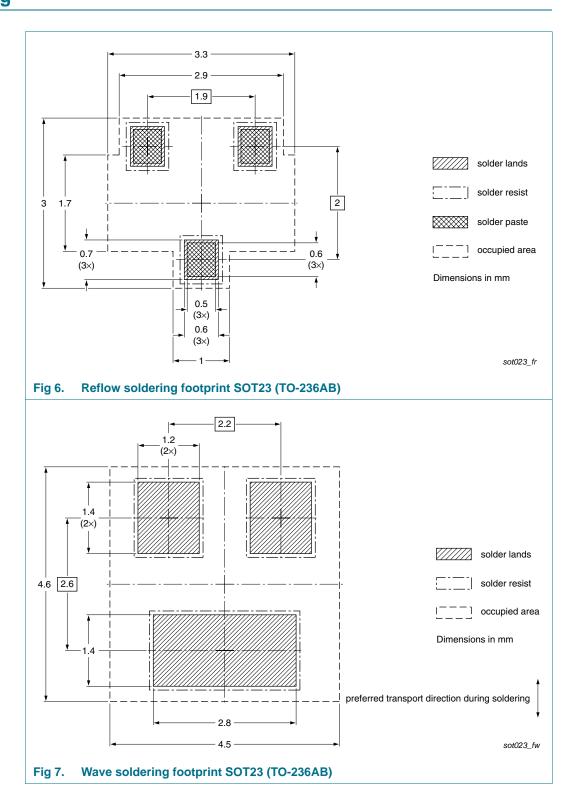
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	uantity
			3000	10000
PDTB123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section } 14}$ .

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## 11. Soldering



PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB123ET v.3	20100922	Product data sheet	-	PDTB123E_SER_2
Modifications:	<ul> <li>Type numbers</li> </ul>	PDTB123EK and PDTB123	3ES deleted.	
	• Table 7 "Charac	cteristics": unit for V <sub>CEsat</sub> ch	nanged from mV to V.	
	<ul> <li>Section 8 "Test</li> </ul>	information": added.		
	<ul> <li>Section 11 "Sol</li> </ul>	dering": added.		
	<ul> <li>Section 13 "Leg</li> </ul>	gal information": updated.		
PDTB123E_SER_2	20091116	Product data sheet	-	PDTB123E_SER_1
PDTB123E_SER_1	20050427	Product data sheet	-	-

#### PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTB123FT

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PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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**NXP Semiconductors** 

# PDTB123ET

### PNP 500 mA resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

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